Abstracts

A C-Band 25 Watt Linear Power FET

Y. Taniguchi, Y. Hasegawa, Y. Aoki and J. Fukaya. "A C-Band 25 Watt Linear Power FET." 1990 MTT-S International Microwave Symposium Digest 90.3 (1990 Vol. III [MWSYM]): 981-984.

A novel four-way power combiner/divider based on 1/8-wavelength transmission line consideration is applied to the design of internally matched GaAs FETs. The resultant FET delivers an output power at 1 dB gain compression point of 44 dBm (25 W) with 12 dB linear gain, 40 % power added efficiency, and -46 dBc 3rd order intermodulation distortion at an output power of 35 dBm (single carrier level), over the 4.4 to 5.0 GHz frequency range.

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